

END OF LIFE

International
IR Rectifier

PD - 96112B

IRF7413QPbF

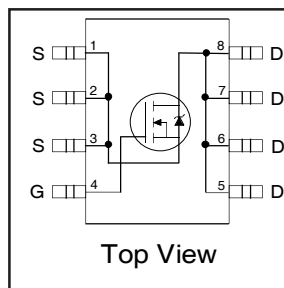
HEXFET® Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- N Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- 150°C Operating Temperature
- Lead-Free

Description

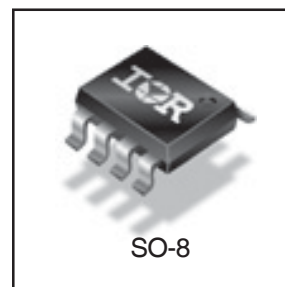
These HEXFET® Power MOSFET's in SO-8 package utilize the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of these HEXFET Power MOSFET's are a 150°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These benefits combine to make this design an extremely efficient and reliable device for use in a wide variety of applications.

The efficient SO-8 package provides enhanced thermal characteristics making it ideal in a variety of power applications. This surface mount SO-8 can dramatically reduce board space and is also available in Tape & Reel.



$$V_{DS} = 30V$$

$$R_{DS(on)} = 0.011\Omega$$



Base part number	Orderable part number	Package Type	Standard Pack		EOL Notice	Replacement Part Number
			Form	Quantity		
IRF7413QPbF	IRF7413QTRPbF	SO-8	Tape and Reel	4000	EOL 529	Please search the EOL part number on IR's website for guidance
	IRF7413QPbF	SO-8	Tube	95	EOL 529	

Absolute Maximum Ratings

Symbol	Parameter	Max	Units
V_{DS}	Drain-to-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	± 20	
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	13	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	9.2	
I_{DM}	Pulsed Drain Current ①	58	
$P_D @ T_A = 25^\circ C$	Power Dissipation	2.5	W
	Linear Derating Factor	0.02	mW/°C
E_{AS}	Single Pulse Avalanche Energy ②	260	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to +150	°C

Thermal Resistance Ratings

Symbol	Parameter	Typ	Max	Units
$R_{\theta JL}$	Junction-to-Drain Lead ④	—	20	°C/W
$R_{\theta JA}$	Junction-to-Ambient ⑤⑥	—	50	

END OF LIFE

IRF7413QPbF

International
IR Rectifier

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min	Typ	Max	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.034	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	0.011	Ω	V _{GS} = 10V, I _D = 7.3A ④
		—	—	0.018		V _{GS} = 4.5V, I _D = 3.7A ④
V _{GS(th)}	Gate Threshold Voltage	1.0	—	3.0	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Transconductance	10	—	—	S	V _{DS} = 10V, I _D = 3.7A
I _{DSS}	Drain-to-Source Leakage Current	—	—	12	μA	V _{DS} = 30V, V _{GS} = 0V
		—	—	25		V _{DS} = 24V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	V _{GS} = -20V
	Gate-to-Source Reverse Leakage	—	—	100		V _{GS} = 20V
Q _g	Total Gate Charge	—	52	79	nC	I _D = 7.3A
Q _{gs}	Gate-to-Source Charge	—	6.1	9.2		V _{DS} = 24V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	16	23		V _{GS} = 10V, See Fig. 6 and 9 ④
R _G	Gate Resistance	1.2	—	3.7		
t _{d(on)}	Turn-On Delay Time	—	8.6	—	ns	V _{DD} = 15V
t _r	Rise Time	—	50	—		I _D = 7.3A
t _{d(off)}	Turn-Off Delay Time	—	52	—		R _G = 6.2 Ω
t _f	Fall Time	—	46	—		R _G = 2.0Ω, See Fig. 10 ④
C _{iss}	Input Capacitance	—	1800	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	680	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	240	—		f = 1.0MHz, See Fig. 5

Source-Drain Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	3.1	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	58		
V _{SD}	Diode Forward Voltage	—	—	1.0	V	T _J = 25°C, I _S = 7.3A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	—	74	110	ns	T _J = 25°C, I _F = 7.3A
Q _{rr}	Reverse Recovery Charge	—	200	300	nC	di/dt = 100A/μs ③

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Starting T_J = 25°C, L = 9.8mH
R_G = 25Ω, I_{AS} = 7.3A. (See Figure 12)

③ I_{SD} ≤ 7.3A, di/dt ≤ 100A/μs, V_{DD} ≤ V_{(BR)DSS},
T_J ≤ 150°C

④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

⑤ Surface mounted on FR-4 board

⑥ R_θ is measured at T_J approximately 90°C

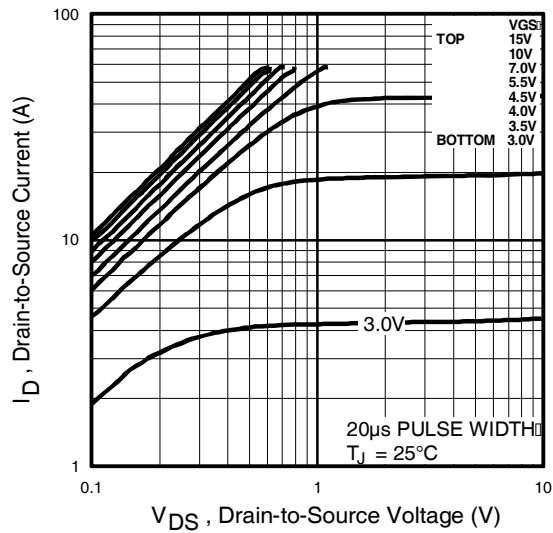


Fig 1. Typical Output Characteristics

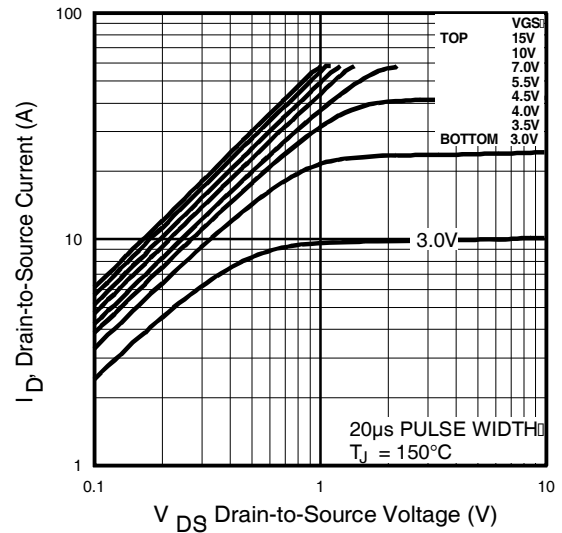


Fig 2. Typical Output Characteristics

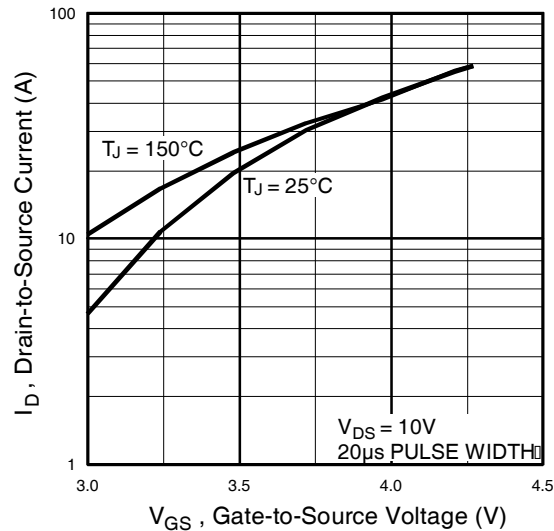


Fig 3. Typical Transfer Characteristics

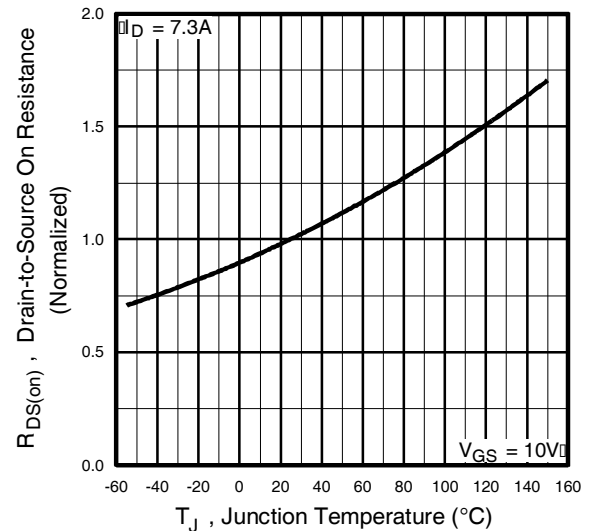


Fig 4. Normalized On-Resistance Vs. Temperature

IRF7413QPbF

International
IR Rectifier

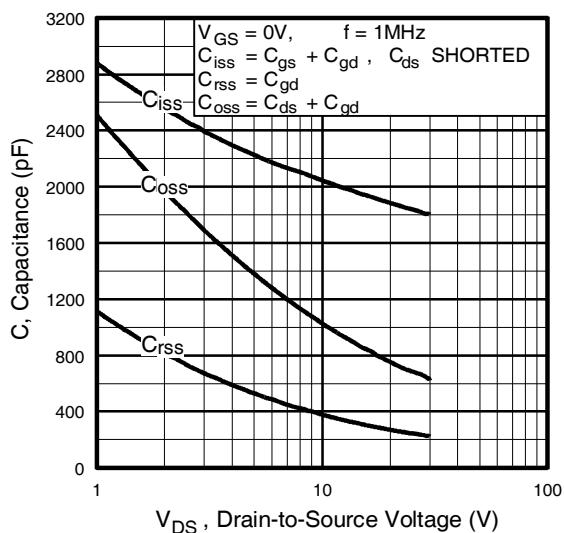


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

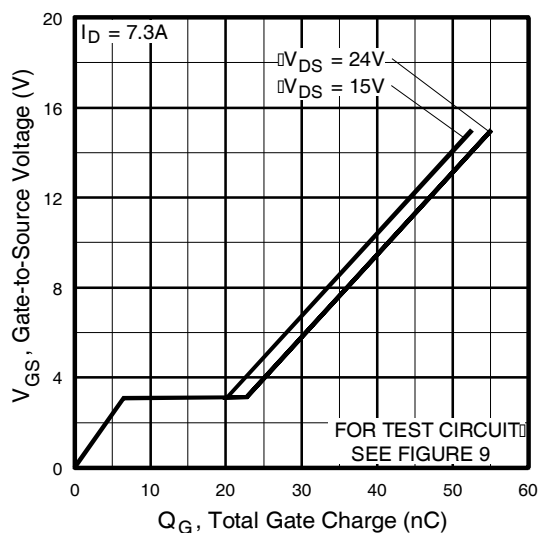


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

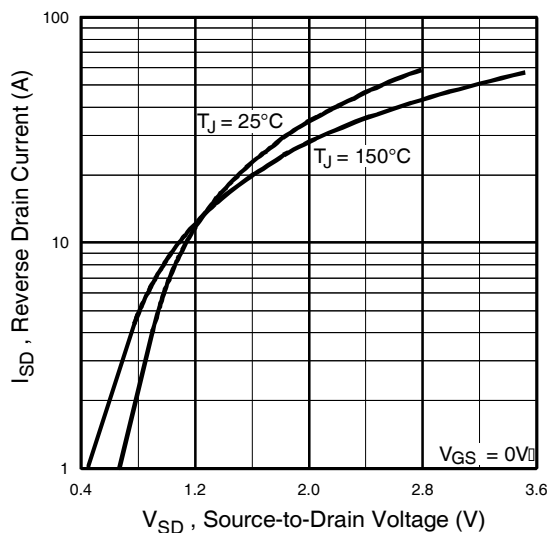


Fig 7. Typical Source-Drain Diode Forward Voltage

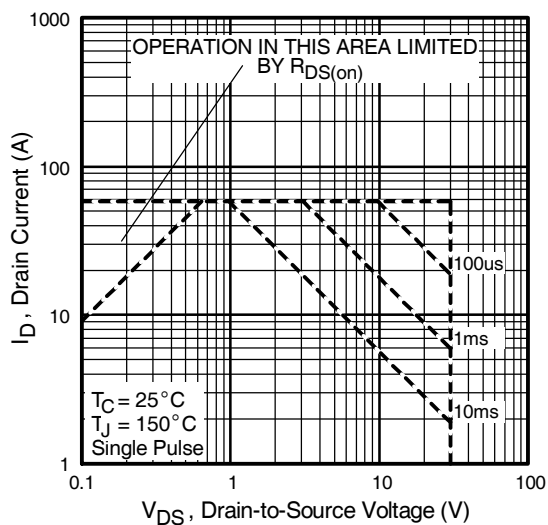


Fig 8. Maximum Safe Operating Area

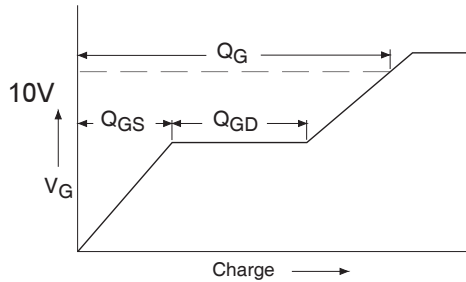


Fig 9a. Basic Gate Charge Waveform

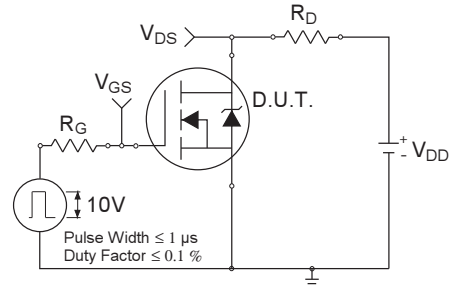


Fig 10a. Switching Time Test Circuit

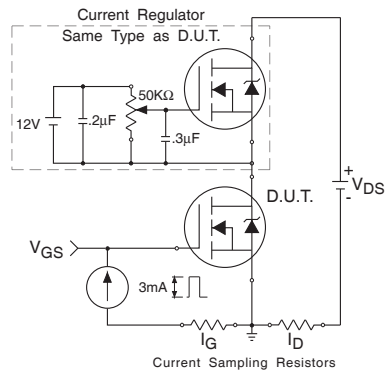


Fig 9b. Gate Charge Test Circuit

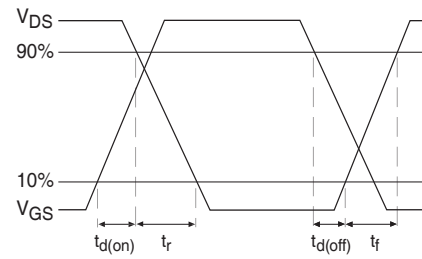


Fig 10b. Switching Time Waveforms

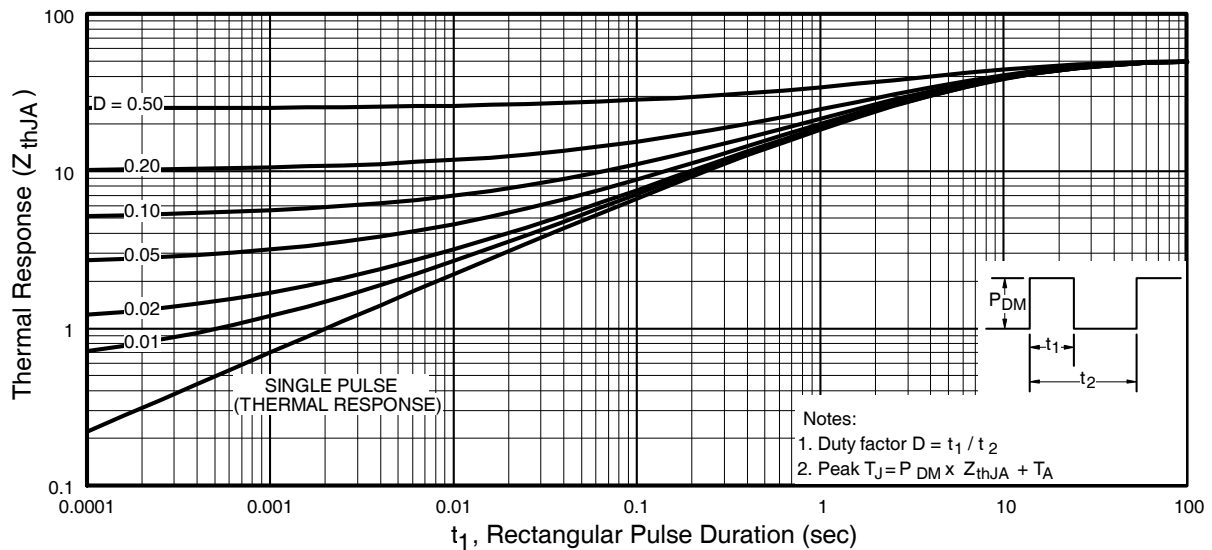


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

IRF7413QPbF

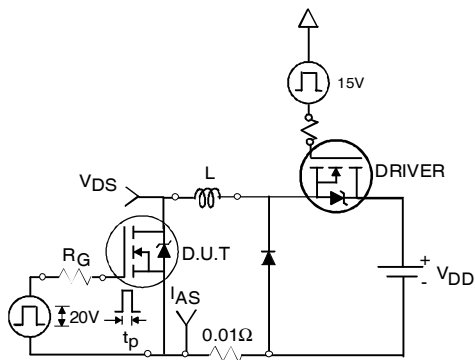


Fig 12a. Unclamped Inductive Test Circuit

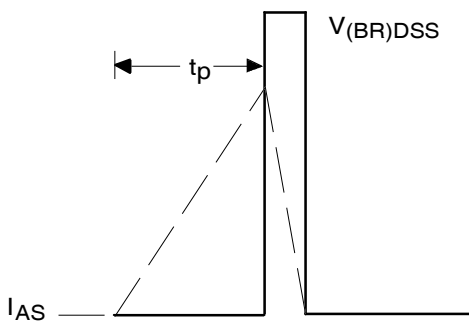


Fig 12b. Unclamped Inductive Waveforms

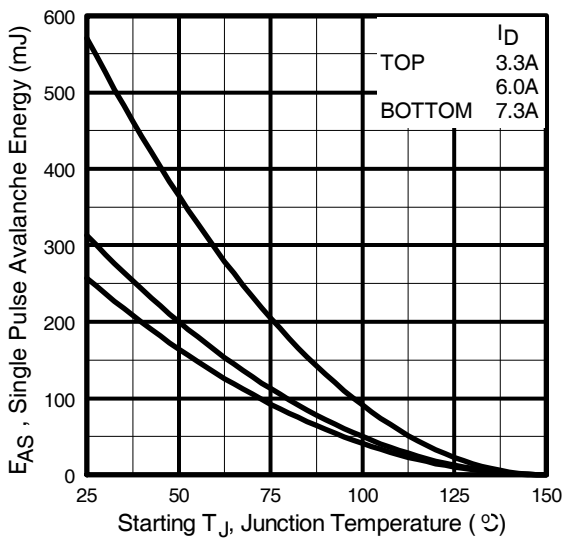


Fig 12c. Maximum Avalanche Energy
Vs. Drain Current

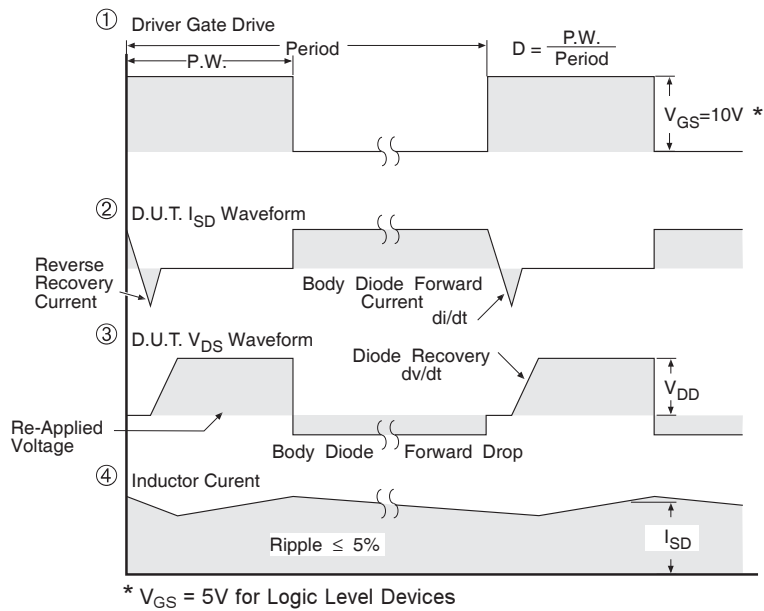
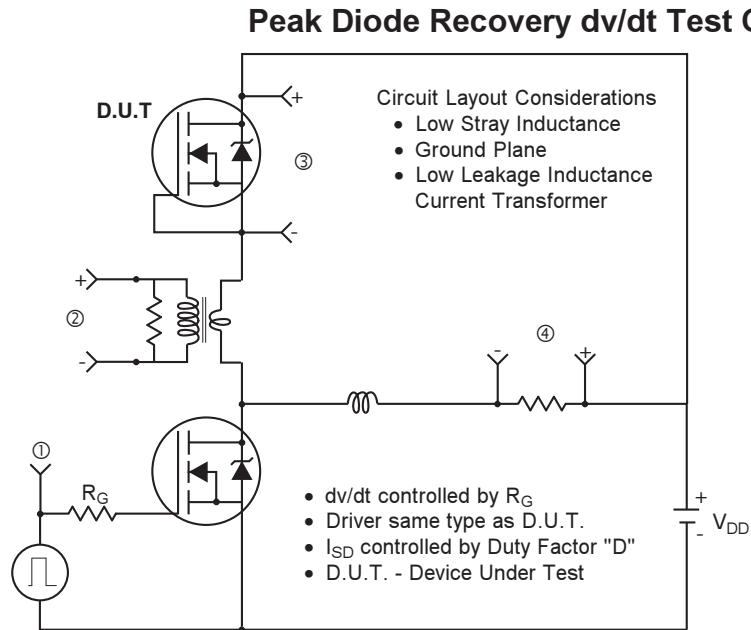


Fig 13. For N-Channel HEXFETS

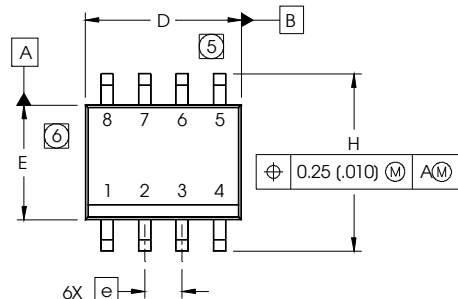
END OF LIFE

IRF7413QPbF

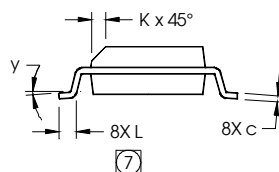
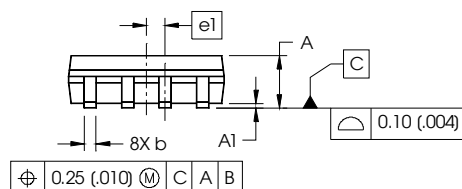
International
IOR Rectifier

SO-8 Package Details

Dimensions are shown in millimeters (inches)



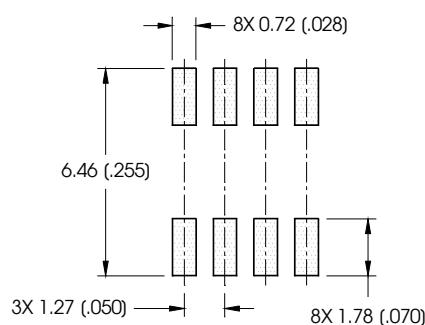
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
v	0°	8°	0°	8°



NOTES:

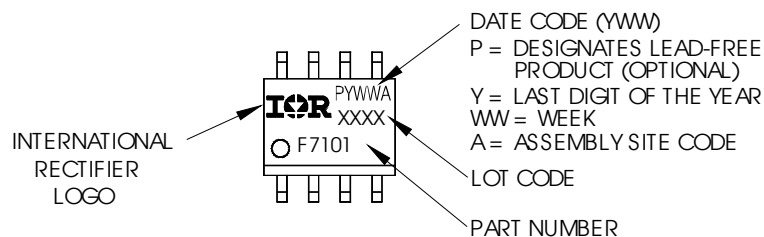
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS.
MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS.
MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO
A SUBSTRATE.

FOOTPRINT



SO-8 Part Marking

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

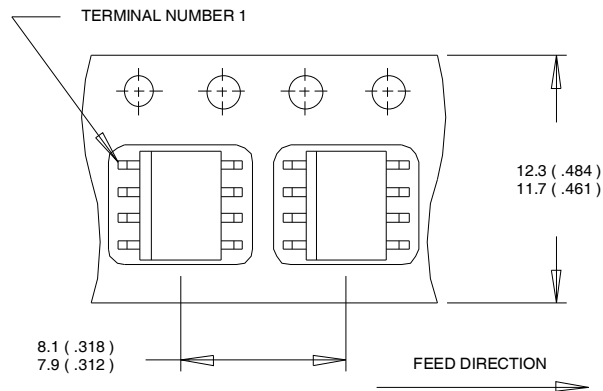


Notes:

1. For an Automotive Qualified version of this part please see <http://www.irf.com/product-info/auto/>
2. For the most current drawing please refer to IR website at <http://www.irf.com/package/>

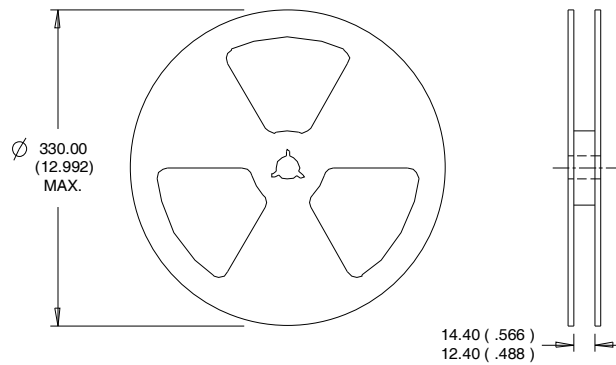
SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



NOTES:

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES:

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

For the most current drawing please refer to IR website at <http://www.irf.com/package/>

END OF LIFE

IRF7413QPbF

International
IR Rectifier

Qualification Information[†]

Qualification level	Industrial [†]	
	(per JEDEC JESD47F ^{††} guidelines)	
Moisture Sensitivity Level	SO-8	MSL1 (per JEDEC J-STD-020D ^{††})
RoHS Compliant	Yes	

[†] Qualification standards can be found at International Rectifier's web site
<http://www.irf.com/product-info/reliability>

^{††} Applicable version of JEDEC standard at the time of product release.

Revision History

Date	Comments
6/17/2014	• Added ordering information to reflect the End-Of-life

International
IR Rectifier

IR WORLD HEADQUARTERS: 101 N. Sepulveda Blvd., El Segundo, California 90245, USA
To contact International Rectifier, please visit <http://www.irf.com/whoto-call/>